#### SILICON (Si) POWER MOSFET A CEB05N65



# **CEB05N65**

## 650V **Δ** 2Ω **Δ** 4.5A **Δ** Si MOSFET

SILICON Si MOSFET ▲ SMD type N-channel enhancement mode UL94V-0 rated flame retardant epoxy TO263 (D2PAK) package ▲ MSL 3 Super high dense cell density for extremely low R<sub>DS(ON)</sub> High power and current handling capability





FREE

RoHS

#### **MAXIMUM RATINGS**

Parameter (T <sub>c</sub> = 25°C, unless otherwise noted)	Characteristics	
Drain-Source Voltage	V <sub>DS</sub>	650V
Gate-Source Voltage	V <sub>GS</sub>	±30V
Continuous Drain Current at T <sub>c</sub> = 25°C	Ι <sub>D</sub>	4.5A
Continuous Drain Current at T <sub>c</sub> = 100°C	Ι <sub>D</sub>	2.9A
Pulsed Drain Current Note 1	IDM Note 5	18A
Maximum Power Dissipation at T <sub>c</sub> = 25°C	PD	84W
Power Dissipation Derating above 25°C	ΔΡ <sub>D</sub>	0.67W/°C
Single Pulsed Avalanche Energy Note 6	E <sub>AS</sub>	43mJ
Single Pulsed Avalanche Current Note 6	I <sub>AS</sub>	3.5A
Operating and Storage Temperature Range	T <sub>J</sub> , T <sub>STG</sub>	-55°C to +150°C

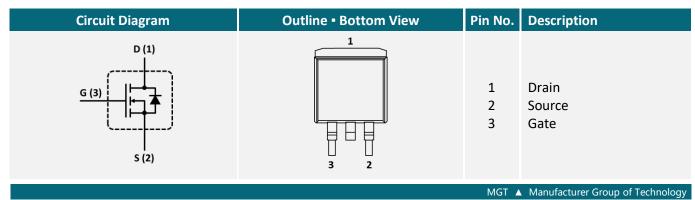
#### THERMAL CHARACTERISTICS

Parameter	Symbol	Limit
Thermal Resistance, Junction-to-Case	R <sub>TH_JC</sub>	1.5°C/W
Thermal Resistance, Junction-to-Ambient	R <sub>th_ja</sub>	62.5°C/W

#### **APPLICATIONS**



#### **PIN DESCRIPTION**



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#### **ELECTRICAL CHARACTERISTICS** A T<sub>c</sub> = 25°C, unless otherwise noted

Item	Condition	Symbol	Min.	Тур.	Max.	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	$V_{GS} = 0V, I_D = 250\mu A$	BV <sub>DSS</sub>	650			V
Zero Gate Voltage Drain Current	$V_{DS} = 650V, V_{GS} = 0V$	I <sub>DSS</sub>			25	μΑ
Gate Body Leakage Current, Forward	$V_{GS} = 30V, V_{DS} = 0V$	I <sub>GSSF</sub>			100	nA
Gate Body Leakage Current, Reverse	$V_{GS}$ = -30V, $V_{DS}$ = 0V	I <sub>GSSR</sub>			-100	nA
On Characteristics Note 2						
Gate Threshold Voltage	$V_{GS} = V_{DS}$ , $I_D = 250 \mu A$	V <sub>GS(th)</sub>	2		4	V
Static Drain-Source On-Resistance	$V_{GS}$ = 10V, $I_D$ = 3A	R <sub>DS(ON)</sub>		2	2.4	Ω
Dynamic Characteristics Note 3						
Input Capacitance	$V_{DS}$ = 25V, $V_{GS}$ = 0V, f = 1MHz	CISS		590		рF
Output Capacitance	$V_{DS}$ = 25V, $V_{GS}$ = 0V, f = 1MHz	Coss		85		рF
Reverse Transfer Capacitance	$V_{DS}$ = 25V, $V_{GS}$ = 0V, f = 1MHz	C <sub>RSS</sub>		20		pF
Switching Characteristics Note 3						
Turn-On Delay Time	$V_{\text{DD}}$ = 300V, $V_{\text{GS}}$ = 10V, $I_{\text{D}}$ = 4.5A, $R_{\text{G}(\text{ext})}$ = 25 $\Omega$	t <sub>D(ON)</sub>		17	34	ns
Turn-On Rise Time	$V_{DD}$ = 300V, $V_{GS}$ = 10V, $I_D$ = 4.5A, $R_{G(ext)}$ = 25 $\Omega$	t <sub>R</sub>		16	32	ns
Turn-Off Delay Time	$V_{DD}$ = 300V, $V_{GS}$ = 10V, $I_D$ = 4.5A, $R_{G(ext)}$ = 25 $\Omega$	t <sub>D(OFF)</sub>		47	94	ns
Turn-Off Fall Time	$V_{\text{DD}}$ = 300V, $V_{\text{GS}}$ = 10V, $I_{\text{D}}$ = 4.5A, $R_{\text{G}(\text{ext})}$ = 25 $\Omega$	t <sub>F</sub>		17.5	35	ns
Total Gate Charge	$V_{DS}$ = 480V, $V_{GS}$ = 10V, $I_{D}$ = 4.5A	Q <sub>G</sub>		13	17	nC
Gate Source Charge	$V_{DS}$ = 480V, $V_{GS}$ = 10V, $I_D$ = 4.5A	Q <sub>GS</sub>		2		nC
Gate Drain Charge	$V_{DS}$ = 480V, $V_{GS}$ = 10V, $I_{D}$ = 4.5A	$\mathbf{Q}_{GD}$		5		nC
Drain-Source Diode Characteristics a	nd Maximum Ratings					
Drain-Source Diode		ls			4.5	А
Forward Current		IS			4.5	A
Drain-Source Diode Forward Voltage Note 2	$V_{GS} = 0V, I_{S} = 2A$	$V_{\text{SD}}$			1.5	V

#### Notes

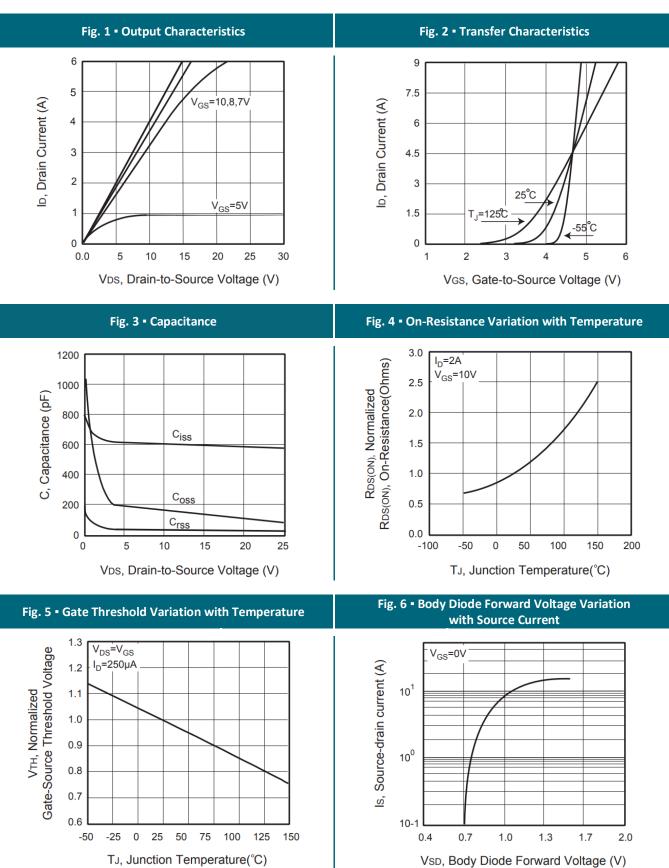
- 1: Repetitive Rating: Pulse width limited by maximum junction temperature
- 2: Pulse Test: Pulse Width ≤ 300µs, Duty Cycle ≤ 2%.
- 3: Guaranteed by design, not subject to production testing.
- 4: Limited only by maximum temperature allowed.
- 5: Pulse width limited by safe operating area.
- 6: L = 7mH,  $I_{AS}$  = 3.5A,  $V_{DD}$  = 50V,  $R_G$  = 25 $\Omega$ , Starting  $T_J$  = 25°C



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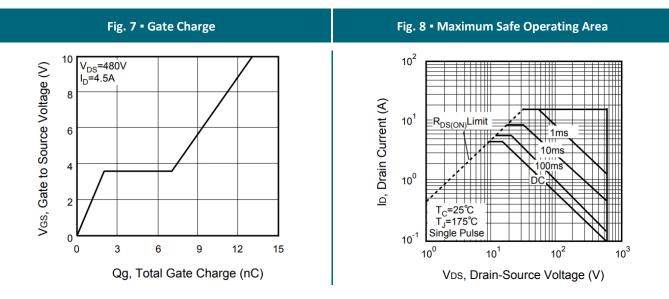
#### **REFERENCE DATA ▲ TYPICAL DEVICE PERFORMANCE**



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#### **REFERENCE DATA ▲ TYPICAL DEVICE PERFORMANCE**



#### Fig. 9 - Switching Test Circuit

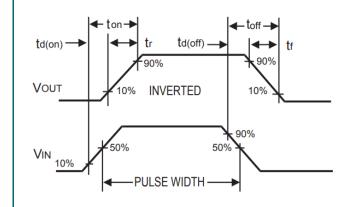
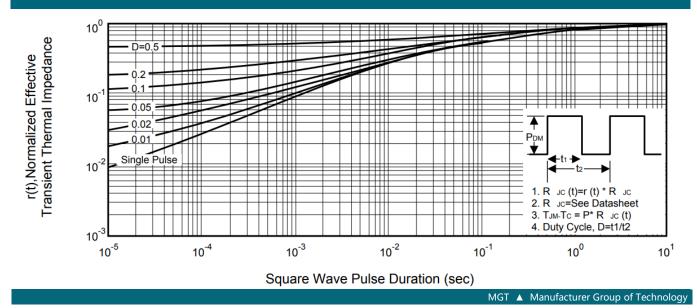


Fig. 10 - Switching Waveforms

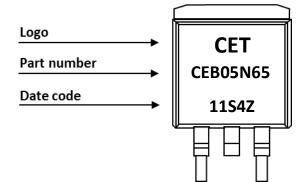
#### Fig. 11 • Normalized Thermal Transient Impedance Curve



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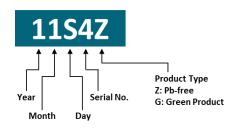


## **PART MARKING**



## DATE CODE

Example: 11S4Z



Coding list for "Day"

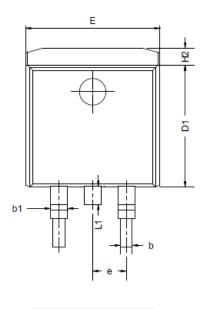
<b>1</b>	<b>2</b>	<b>3</b>	<b>4</b>	<b>5</b>	<b>6</b>	<b>7</b>	<b>8</b>	<b>9</b>	<b>A</b>
01	02	03	04	05	06	07	08	09	10
<b>B</b>	<b>C</b>	<b>D</b>	<b>E</b>	<b>F</b>	<b>G</b>	<b>H</b>	┃	<b>J</b>	<b>K</b>
11	12	13	14	15	16	17	18	19	20
<b>L</b>	<b>M</b>	<b>N</b>	<b>0</b>	<b>P</b>	<b>Q</b>	<b>R</b>	<b>S</b>	<b>T</b>	<b>U</b>
21	22	23	24	25	26	27	28	29	30
<b>V</b> 31									

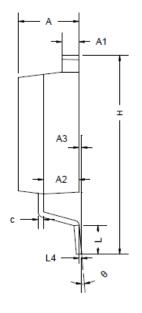
Coding list for "Month"

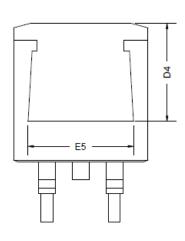
<b>1</b> Jan	<b>2</b> Feb	<b>3</b> Mar	<b>4</b> Apr	<b>5</b> May	<b>6</b> Jun
<b>7</b> Jul	<b>8</b> Aug	<b>9</b> Sep	<b>A</b> Oct	B Nov	<b>C</b> Dec
	Со	ding lis	t for "۱	(ear"	
(	)	1 2	23	34	
20	20 2	021 20	022 20	023 202	24
5	5	6 7	78	39	)
20	25 20	026 20	027 20	28 202	29



#### **PACKAGE OUTLINE**







Sym	Millimeters (Min.)	Millimeters (Typ.)	Millimeters (Max.)	Sym	Millimeters (Min.)	Millimeters (Typ.)	Millimeters (Max.)
А	4.37	4.57	4.77	Е	9.86	10.16	10.36
A1	1.22	1.27	1.42	E5	7.06	-	-
A2	2.49	2.69	2.89	е		2.54 BSC	
A3	0.00	0.13	0.25	Н	14.70	15.10	15.50
b	0.70	0.81	0.96	H2	1.07	1.27	1.47
b1	1.17	1.27	1.47	L	2.00	2.30	2.60
С	0.30	0.38	0.53	L1	1.40	1.55	1.70
D1	8.50	8.70	8.90	L4		0.25 BSC	
D4	6.60	-	-	θ	0°	5°	9°

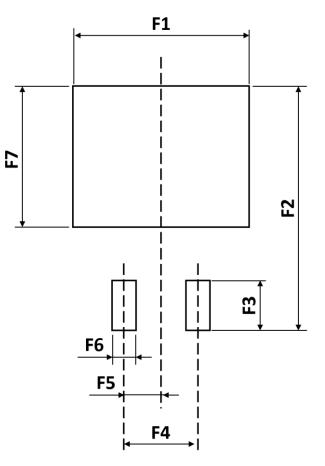
## **ORDERING INFORMATION**

Part Number	Package	Packing	Reel Qty.	Inner Box Qty.	Outer Box Qty.
CEB05N65	TO263 (D2PAK)	Reel	800pcs	800pcs	6,400pcs





### **RECOMMENDED PAD LAYOUT**



Sym	Millimeters (Min.)	Millimeters (Typ.)	Millimeters (Max.)	Sym	Millimeters (Min.)	Millimeters (Typ.)	Millimeters (Max.)
F1	-	12.20	-	F5	-	2.54	-
F2	-	16.90	-	F6	-	1.60	-
F3	-	2.54	-	F7	-	9.75	-
F4	-	5.08	-				

Notes:

1. The suggested land pattern dimensions have been provided for reference only.

2. For further information, please reference document IPC-7351A.

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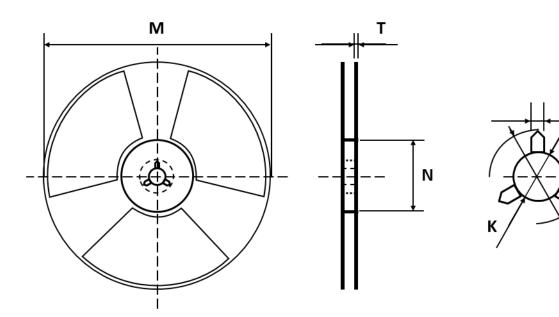


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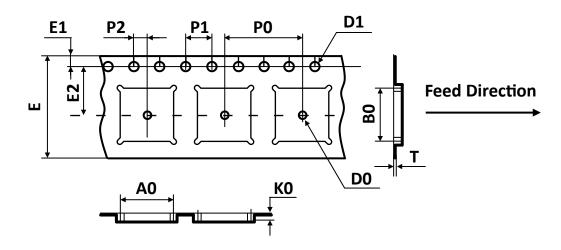


#### **REEL DIMENSIONS** All dimensions in mm



Tape Size	Reel Size	М	N	Т	Н	К	S
		Ø330.00	Ø100.00	2.10	22.00	13.00	2.00
24mm	24mm Ø330	±2.00	±0.50	±0.20	±0.50	+0.50	+0.50
		±2.00	±0.50	±0.20	±0.50	-0.20	-0.20

## TAPE DIMENSIONS All dimensions in mm



Package	A0	B0	К0	D0	D1	E	E1	E2	P0	P1	P2	Т
TO263	10.80	16.30	4.85	1.50	1.55	24.00	1.75	11.50	16.00	4.00	2.00	0.35
(D <sup>2</sup> PAK	±0.10	±0.10	±0.10	±0.10	±0.05	±0.30	±0.10	±0.10	±0.10	±0.10	±0.10	±0.05

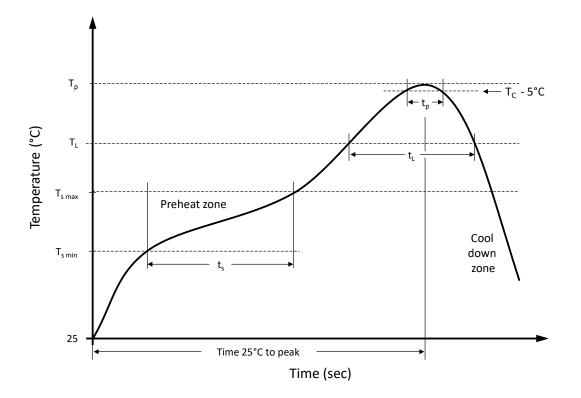


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#### **RECOMMENDED REFLOW SOLDERING PROFILE**



#### **Recommended reflow soldering conditions** ▲ **Refer to JEDEC J-STD-020E**

Profile Features		Sn-Pb Eutetic Assembly	Pb-Free Assembly
Preheat temperature min.	$T_{smin}$	100 °C	150 °C
Preheat temperature max.	$T_{s max}$	150 °C	200 °C
Preheat time $t_s$ from $T_{s min}$ to $T_{s max}$	ts	120 seconds	120 seconds
Ramp-up rate (T <sub>L</sub> to T <sub>p</sub> )		max. 3 °C/second	max. 3 °C/second
Liquidous temperature	ΤL	183 °C	217 °C
Time $t_L$ maintained above $T_L$	t∟	150 seconds max.	150 seconds max.
Peak package body temperature	Tp	235°C	260°C
Timeframe of within 5°C below and up to max actual peak body temperature	tp	20 seconds max.	30 seconds max.
Ramp-down rate ( $T_L$ to $T_p$ )		max. 6 °C/second	max. 6 °C/second
Time 25°C to peak temperature		max. 6 minutes	max. 8 minutes



## **REVISION TABLE**

Revision	Date	Status	Notes
001	30/09/2022	Initial release	Initial publication

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